International
IOR Rectifier

Data Sheet No. PD60227

IRS2117/IRS2118(S)PbF

SINGLE CHANNEL DRIVER

Features

- Floating channel designed for bootstrap operation
- Fully operational to +600 V
- Tolerant to negative transient voltage, dV/dt immune
- Gate drive supply range from 10 V to 20V
- Undervoltage lockout
- CMOS Schmitt-triggered inputs with pull-down
- Output in phase with input (IRS2117) or out of phase with input (IRS2118)
- RoHS compliant

Product Summary

V_{OFFSET}	600 V max.
I_O+/-	200 mA / 420 mA
V_{OUT}	10 V - 20 V
$t_{on/off}$ (typ.)	125 ns & 105 ns

Description

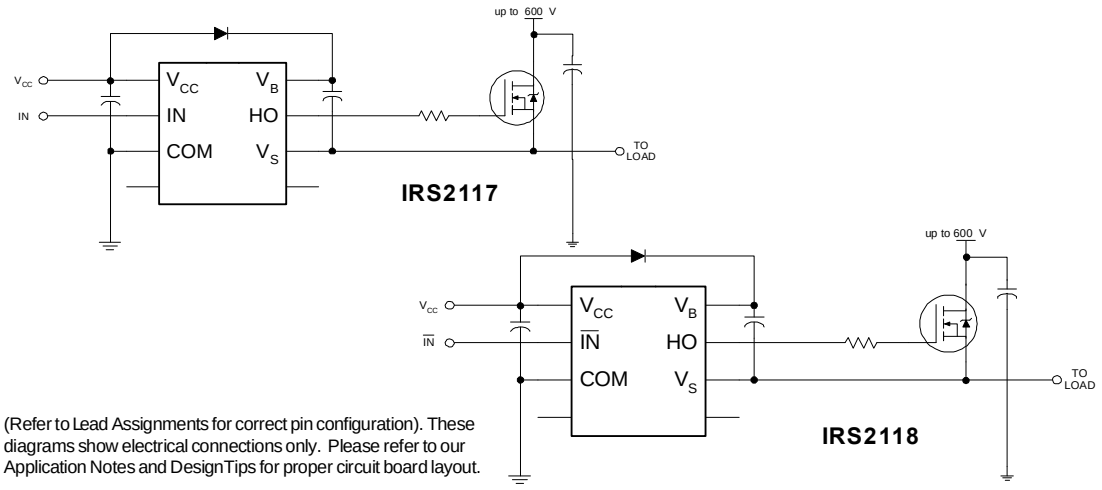
The IRS2117/IRS2118 are a high voltage, high speed power MOSFET and IGBT driver. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The logic input is compatible with standard CMOS outputs. The output driver features a high pulse current buffer stage designed for minimum cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high-side or low-side configuration which operates up to 600 V.

Packages

8-Lead PDIP
IRS2117/IRS2118

8-Lead SOIC
IRS2117S/IRS2118S

Typical Connection



(Refer to Lead Assignments for correct pin configuration). These diagrams show electrical connections only. Please refer to our Application Notes and DesignTips for proper circuit board layout.

Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Additional information is shown in Figs. 5 through 8.

Symbol	Definition		Min.	Max.	Units
V_B	High-side floating supply voltage		-0.3	625	V
V_S	High-side floating supply offset voltage		V_B - 25	V_B + 0.3	
V_{HO}	High-side floating output voltage		V_S - 0.3	V_B + 0.3	
V_{CC}	Logic supply voltage		-0.3	25	
V_{IN}	Logic input voltage		-0.3	V_{CC} + 0.3	
dV_S/dt	Allowable offset supply voltage transient (Fig. 2)		—	50	V/ns
P_D	Package power dissipation @ $T_A \leq +25$ °C	(8 lead PDIP)	—	1.0	W
		(8 lead SOIC)	—	0.625	
Rth_{JA}	Thermal resistance, junction to ambient	(8 lead PDIP)	—	125	°C/W
		(8 lead SOIC)	—	200	
T_J	Junction temperature		—	150	°C
T_S	Storage temperature		-55	150	
T_L	Lead temperature (soldering, 10 seconds)		—	300	

Recommended Operating Conditions

The input/output logic timing diagram is shown in Fig. 1. For proper operation the device should be used within the recommended conditions. The V_S offset rating is tested with all supplies biased at 15 V differential.

Symbol	Definition	Min.	Max.	Units
V_B	High-side floating supply absolute voltage	V_S + 10	V_S + 20	V
V_S	High-side floating supply offset voltage	Note 1	600	
V_{HO}	High-side floating output voltage	V_S	V_B	
V_{CC}	Logic supply voltage	10	20	
V_{IN}	Logic input voltage	0	V_{CC}	
T_A	Ambient temperature	-40	125	°C

Note 1: Logic operational for V_S of -5 V to +600 V. Logic state held for V_S of -5 V to $-V_{BS}$. (Please refer to the Design Tip DT97-3 for more details).

Dynamic Electrical Characteristics

V_{BIAS} (V_{CC}, V_{BS}) = 15 V, C_L = 1000 pF and T_A = 25 °C unless otherwise specified. The dynamic electrical characteristics are measured using the test circuit shown in Fig. 3.

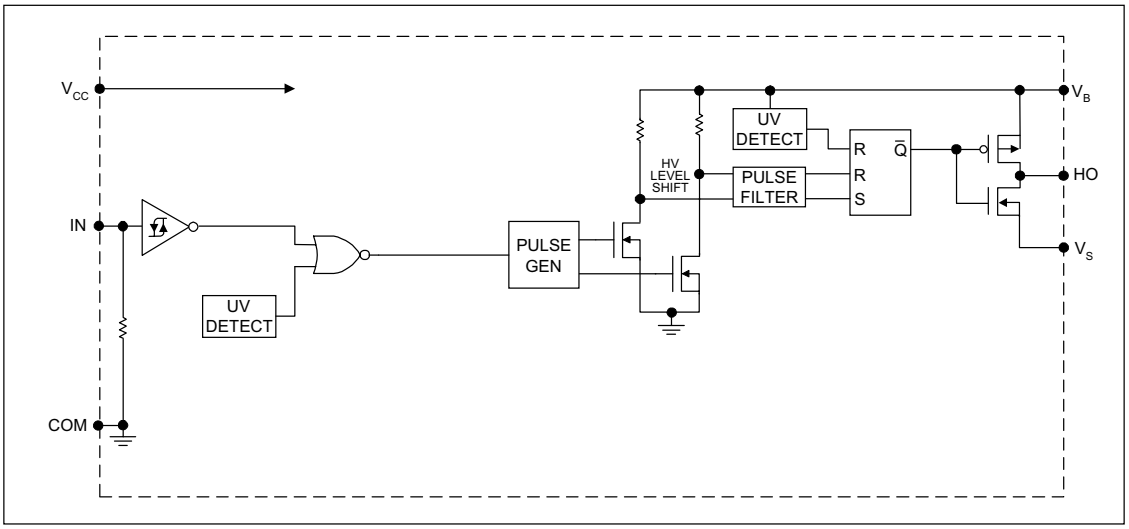
Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
t_{on}	Turn-on propagation delay	—	125	200	ns	V_S = 0 V
t_{off}	Turn-off propagation delay	—	105	180		V_S = 600 V
t_r	Turn-on rise time	—	75	130		
t_f	Turn-off fall time	—	35	65		

Static Electrical Characteristics

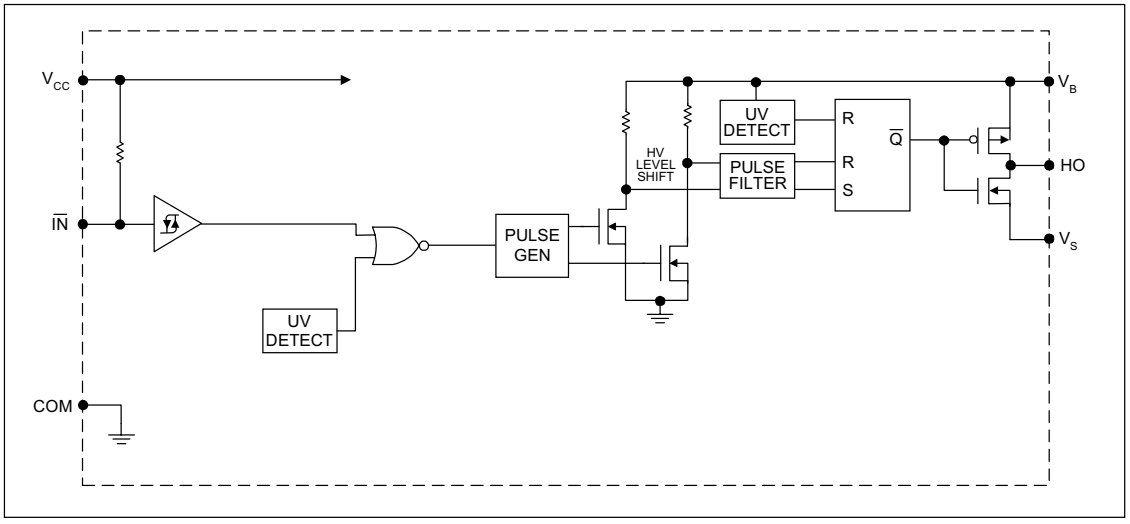
V_{BIAS} (V_{CC}, V_{BS}) = 15 V and T_A = 25 °C unless otherwise specified. The V_{IN}, V_{TH}, and I_{IN} parameters are referenced to COM. The V_O and I_O parameters are referenced to COM and are applicable to the respective output leads: HO or LO.

Symbol	Definition		Min.	Typ.	Max.	Units	Test Conditions
V_{IH}	Input voltage - logic “1” (IRS2117) logic “0” (IRS2118)		9.5	—	—	V	
V_{IL}	Input voltage - logic “0” (IRS2117) logic “1” (IRS2118)		—	—	6.0		
V_{OH}	High level output voltage, V_{BIAS} - V_O		—	0.05	0.2		I_O = 2 mA
V_{OL}	Low level output voltage, V_O		—	0.02	0.1		
I_{LK}	Offset supply leakage current		—	—	50	µA	V_B = V_S = 600 V
I_{QBS}	Quiescent V_{BS} supply current		—	50	240		V_{IN} = 0 V or V_{CC}
I_{QCC}	Quiescent V_{CC} Supply Current		—	70	340		
I_{IN+}	Logic “1” input bias current	(IRS2117)	—	20	40		V_{IN} = V_{CC}
		(IRS2118)					V_{IN} = 0 V
I_{IN-}	Logic “0” input bias current	(IRS2117)	—	—	5.0		
		(IRS2118)					V_{IN} = V_{CC}
V_{BSUV+}	V_{BS} supply undervoltage positive going threshold		7.6	8.6	9.6	V	
V_{BSUV-}	V_{BS} supply undervoltage negative going threshold		7.2	8.2	9.2		
V_{CCUV+}	V_{CC} supply undervoltage positive going threshold		7.6	8.6	9.6		
V_{CCUV-}	V_{CC} supply undervoltage negative going threshold		7.2	8.2	9.2		
IO+	Output high short circuit pulsed current		200	290	—	mA	V_O = 0V V_{IN} = Logic “1” PW ≤ 10 µs
I_{O-}	Output low short circuit pulsed current		420	600	—		V_O = 15V V_{IN} = Logic “0” PW ≤ 10 µs

Functional Block Diagram (IRS2117)



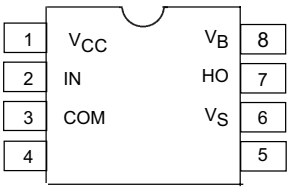
Functional Block Diagram (IRS2118)



Lead Definitions

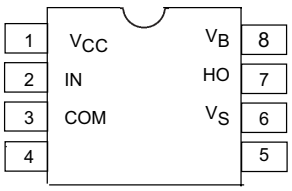
Symbol	Description
V_{CC}	Logic and gate drive supply
IN	Logic input for gate driver output (HO), in phase with HO (IRS2117)
$\overline{IN}$	Logic input for gate driver output (HO), out of phase with HO (IRS2118)
COM	Logic ground
V_B	High-side floating supply
HO	High-side gate drive output
V_S	High-side floating supply return

Lead Assignments



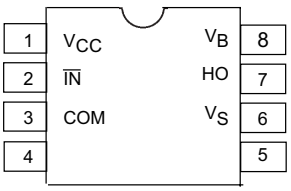
8 Lead PDIP

IRS2117



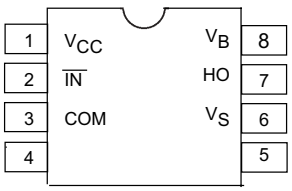
8 Lead SOIC

IRS2117S



8 Lead PDIP

IRS2118



8 Lead SOIC

IRS2118S

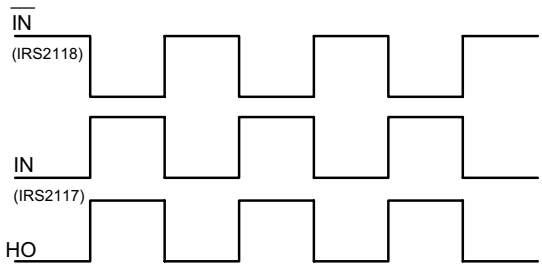


Figure 1. Input/Output Timing Diagram

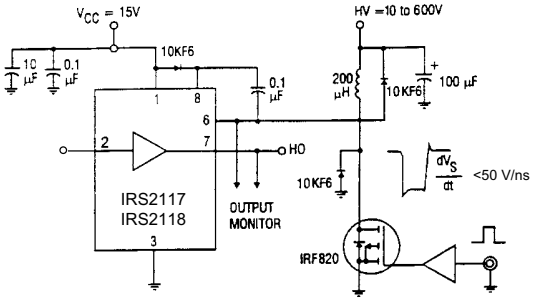


Figure 2. Floating Supply Voltage Transient Test Circuit

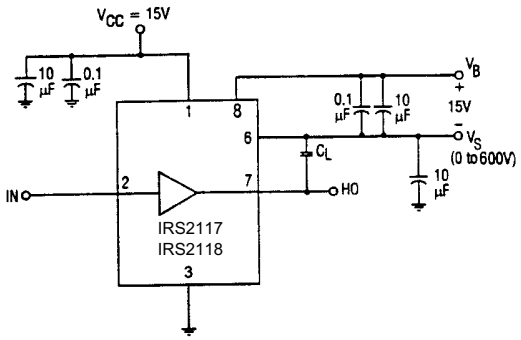


Figure 3. Switching Time Test Circuit

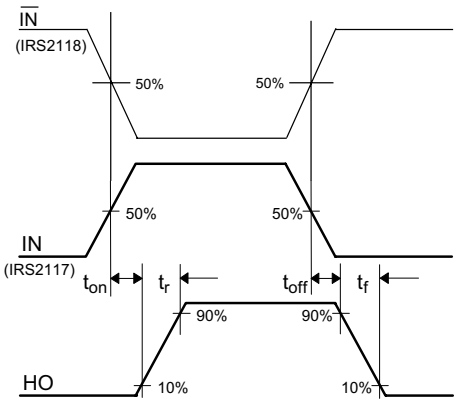


Figure 4. Switching Time Waveform Definition

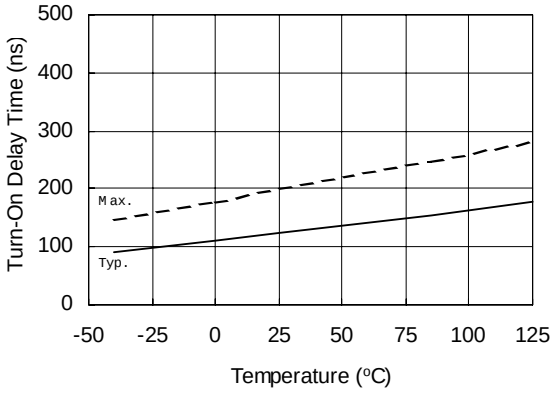


Figure 5A. Turn-On Time vs. Temperature

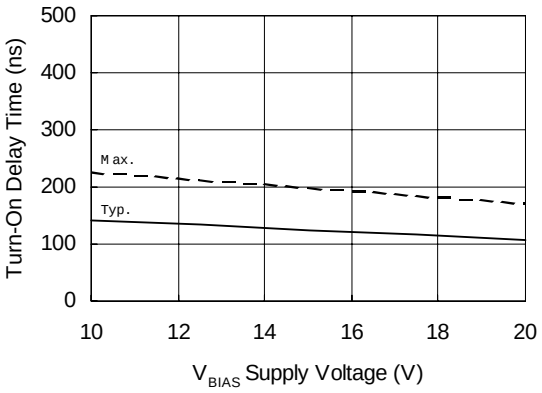


Figure 5B. Turn-On Time vs. Supply Voltage

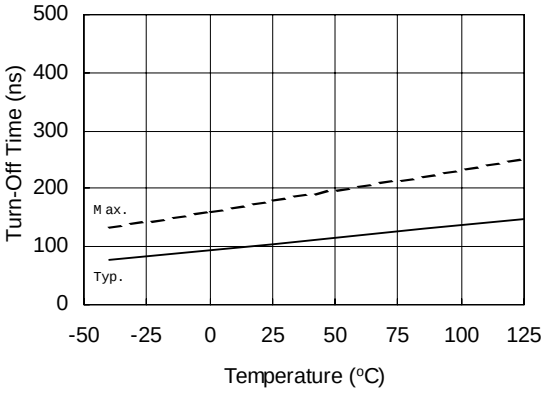


Figure 6A. Turn-Off Time vs. Temperature

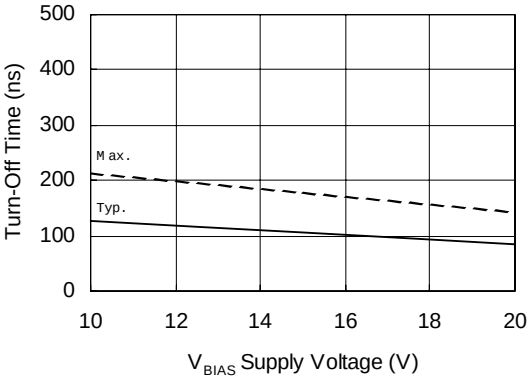


Figure 6B. Turn-Off Time vs. Supply Voltage

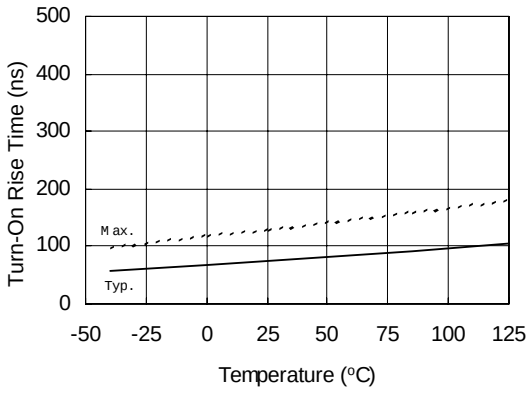


Figure 7A. Turn-On Rise Time vs.Temperature

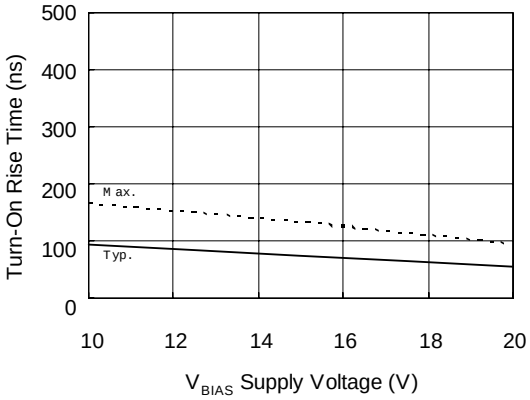


Figure 7B. Turn-On Rise Time vs. Supply Voltage

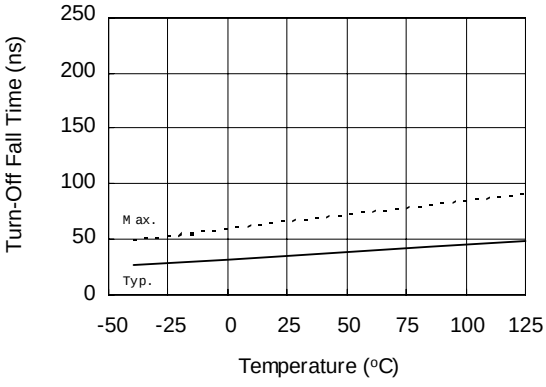


Figure 8A. Turn-Off Fall Time vs. Temperature

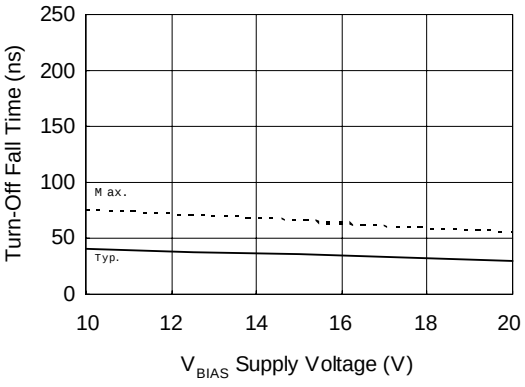


Figure 8B. Turn-Off Fall Time vs. Supply Voltage

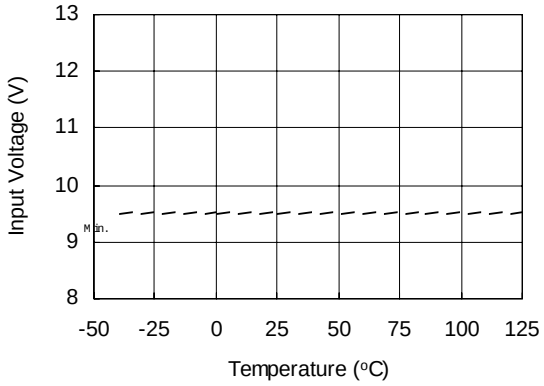


Figure 9A. Logic "1" (IRS2118 "0") Input Voltage vs. Temperature

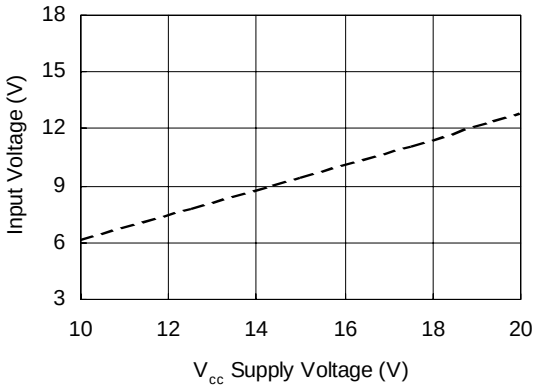


Figure 9B. Logic "1" (IRS2118 "0") Input Voltage vs. Supply Voltage

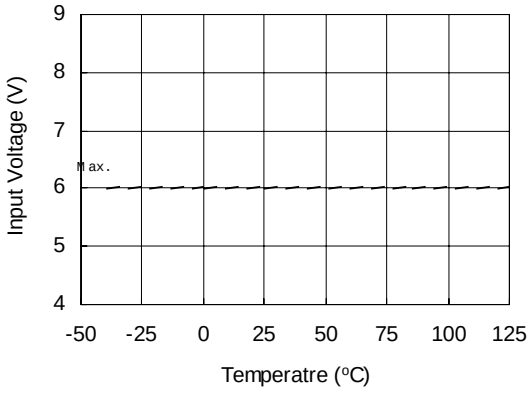


Figure 10A. Logic "0" (IRS2118 "1") Input Voltage vs. Temperature

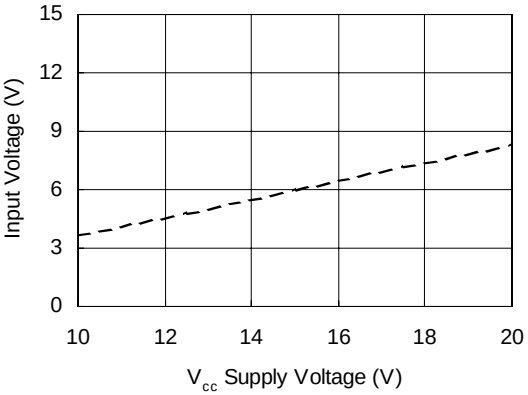


Figure 10B. Logic "0" (IRS2118 "1") Input Voltage vs. Supply Voltage

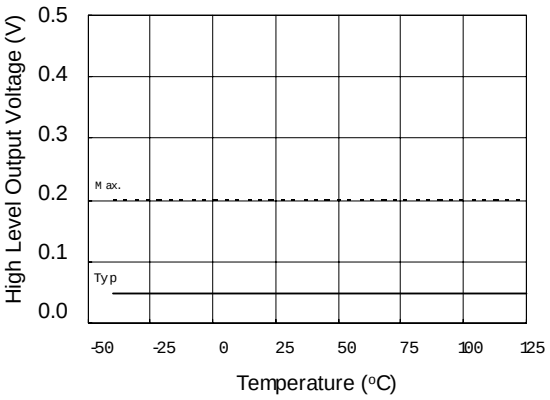


Figure 11A. High Level Output vs. Temperature (I_O = 2 mA)

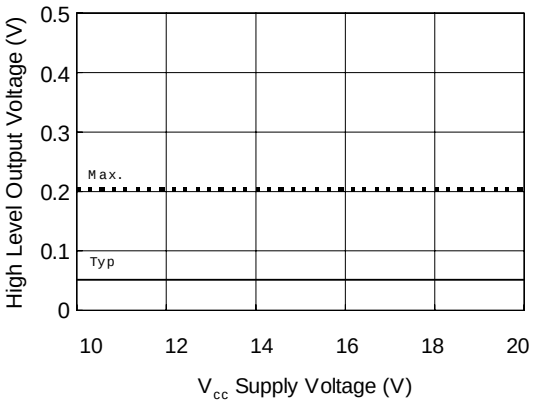


Figure 11B. High Level Output vs. Supply Voltage (I_O = 2 mA)

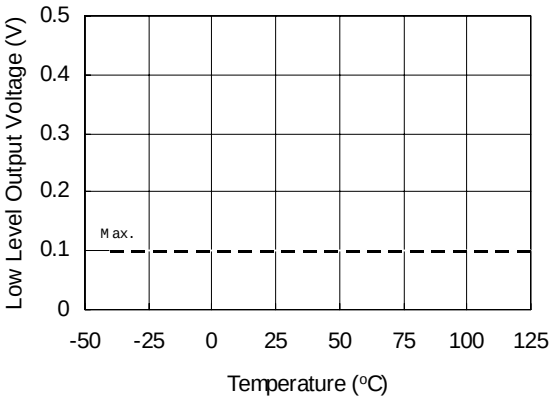


Figure 12A. Low Level Output vs.Temperature

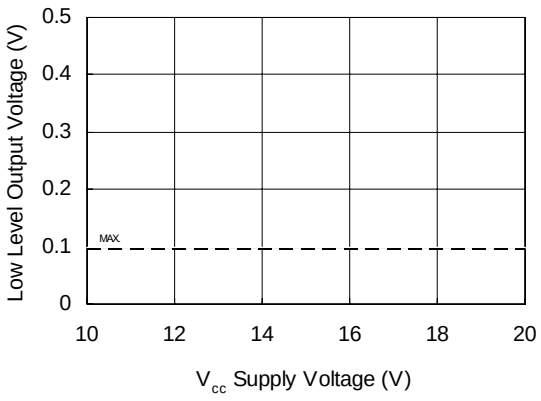


Figure 12B. Low Level Output vs. Supply Voltage

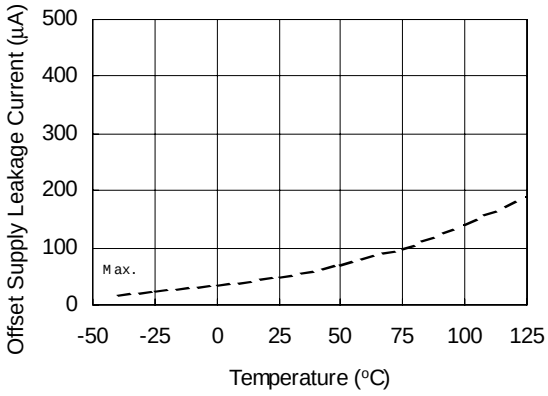


Figure 13A. Offset Supply Leakage Current vs. Temperature

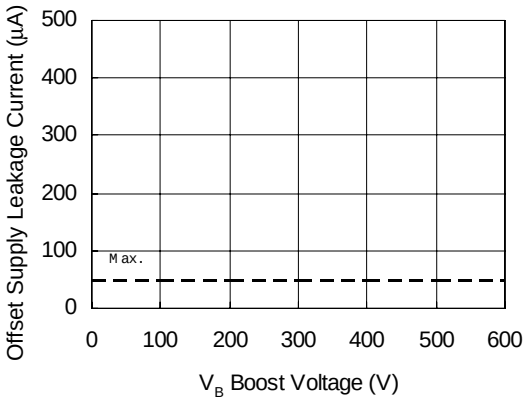


Figure 13B. Offset Supply Leakage Current vs. V_B Boost Voltage

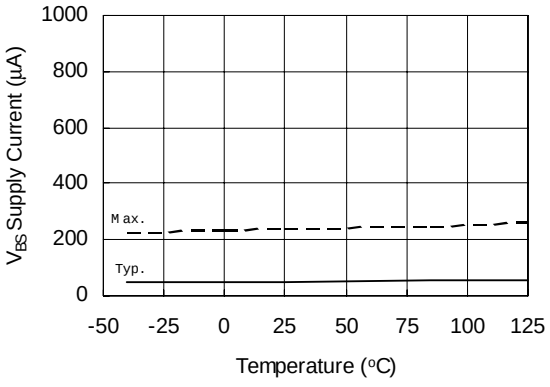


Figure 14A. V_{BS} Supply Current vs. Temperature

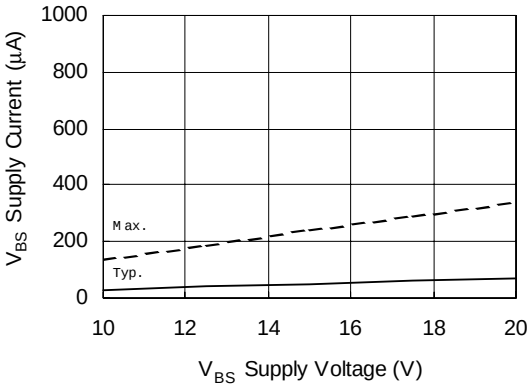


Figure 14B. V_{BS} Supply Current vs. Supply Voltage

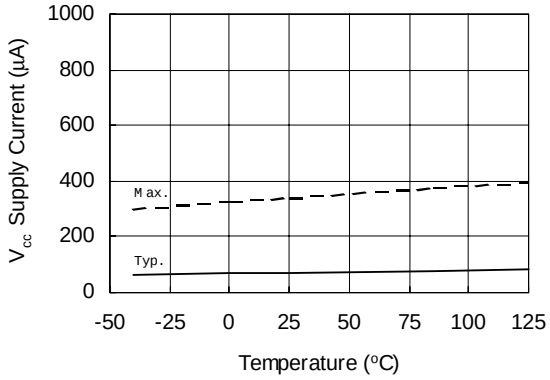


Figure 15A. V_{CC} Supply Current vs. Temperature

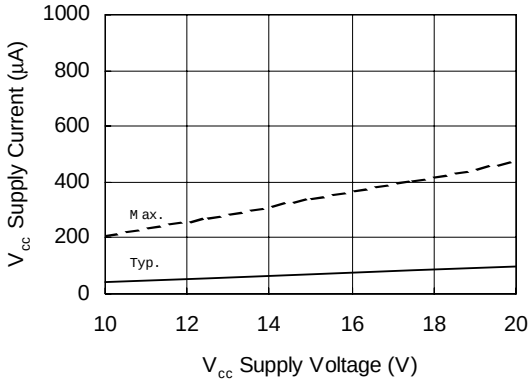


Figure 15B. V_{CC} Supply Current vs. Supply Voltage

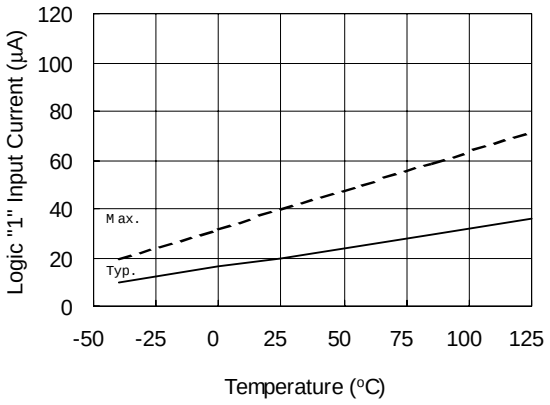


Figure 16A. Logic "1" (IRS2118 Logic"0") Input Current vs. Temperature

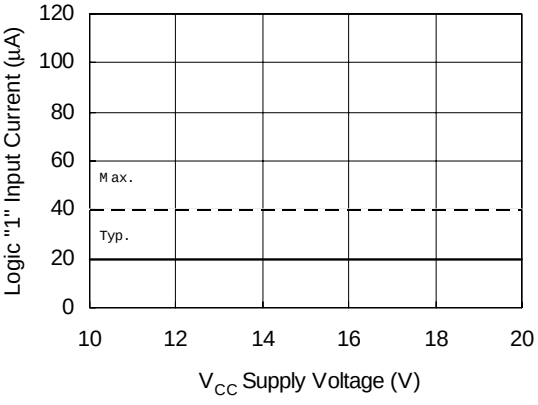


Figure 16B. Logic "1" (IRS2118 Logic "0") Input Current vs. Supply Voltage

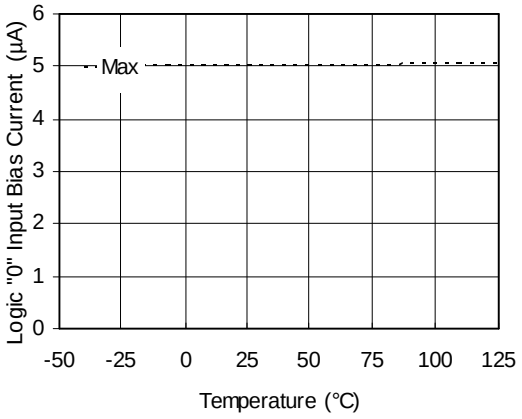


Figure 17A. Logic "0" Input Bias Current vs. Temperature

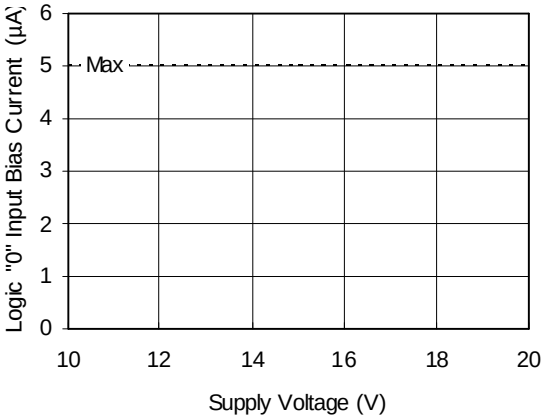


Figure 17B. Logic "0" Input Bias Current vs. Voltage

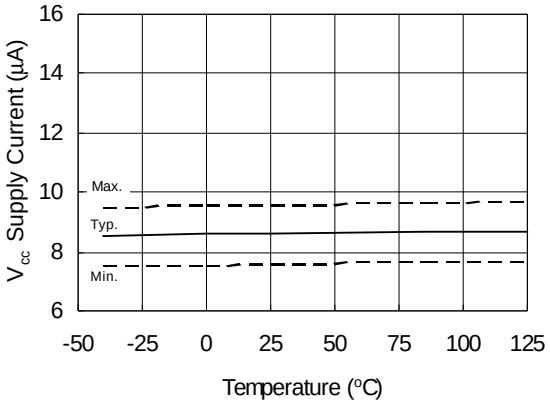


Figure 18. V_{cc} Undervoltage Threshold (+) vs. Temperature

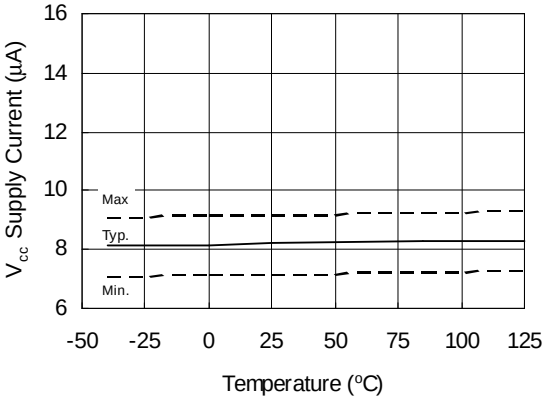


Figure 19. V_{cc} Undervoltage Threshold (-) vs. Temperature

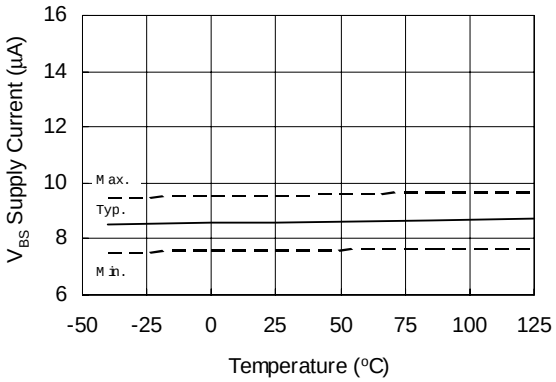


Figure 20. V_{BS} Undervoltage Threshold (+) vs. Temperature

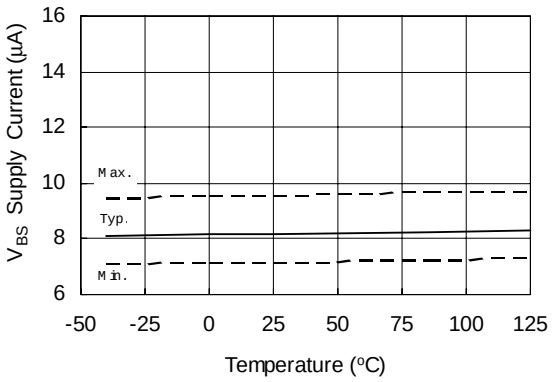


Figure 21. V_{BS} Undervoltage Threshold (-) vs. Temperature

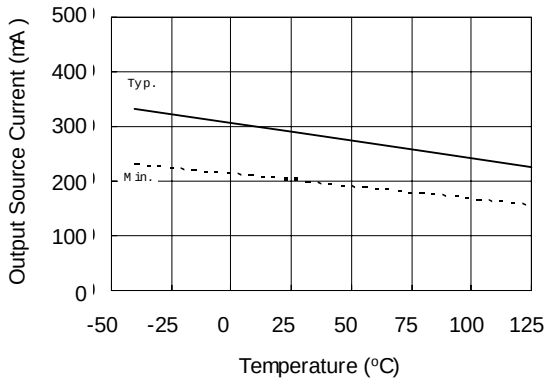


Figure 22A. Output Source Current vs. Temperature

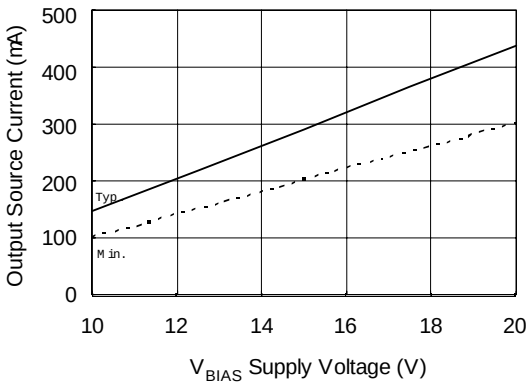


Figure 22B. Output Source Current vs. Supply Voltage

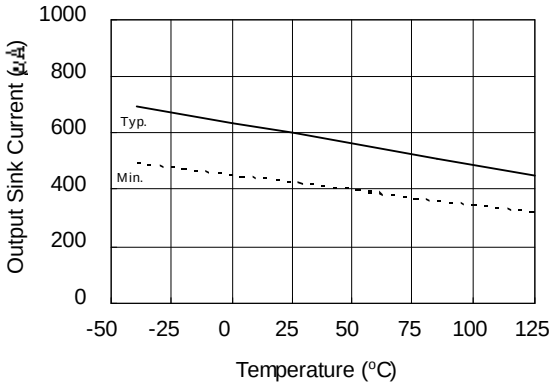


Figure 23A. Output Sink Current vs.Temperature

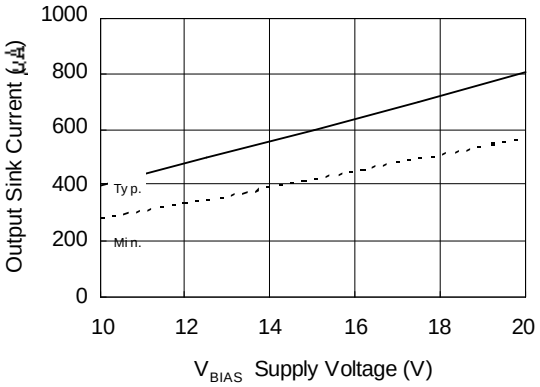


Figure 23B. Output Sink Current vs. Supply Voltage

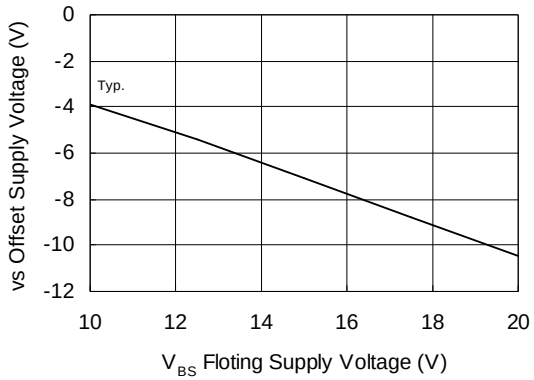


Figure 24. Maximum VS Negative Offset vs. Supply Voltage

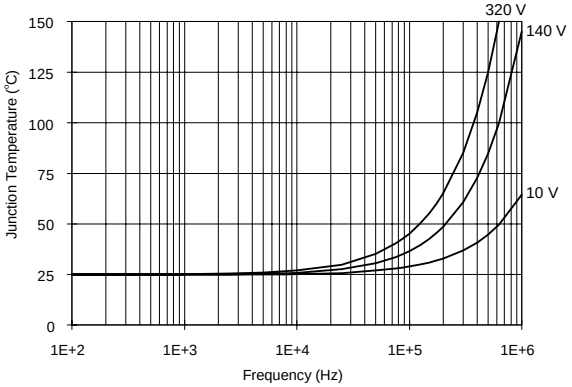


Figure 24. IRS2117/IRS2118 T_J vs. Frequency (IRFBC20)
R_{GATE} = 33 Ω, V_{CC} = 15 V

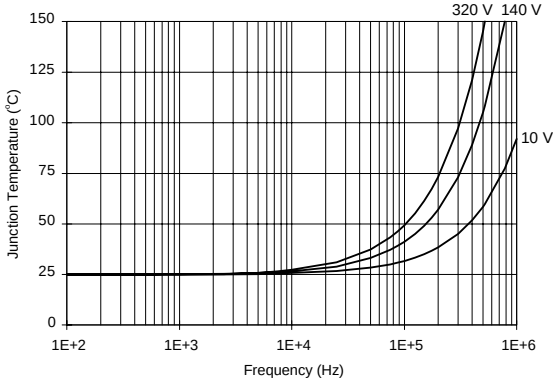


Figure 25. IRS2117/IRS2118 T_J vs. Frequency (IRFBC30)
R_{GATE} = 22 Ω, V_{CC} = 15 V

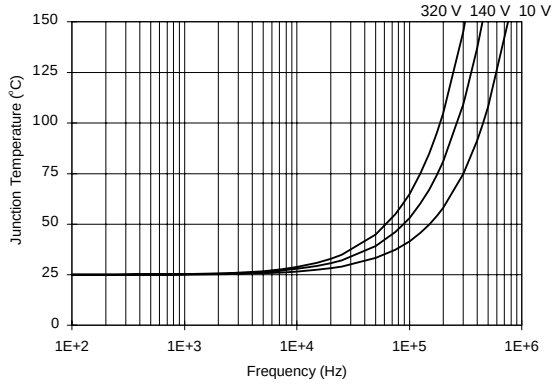


Figure 26. IRS2117/IRS2118 T_J vs. Frequency (IRFBC40)
R_{GATE} = 15 Ω, V_{CC} = 15 V

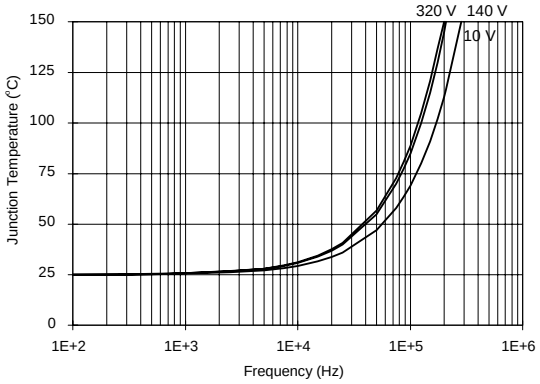
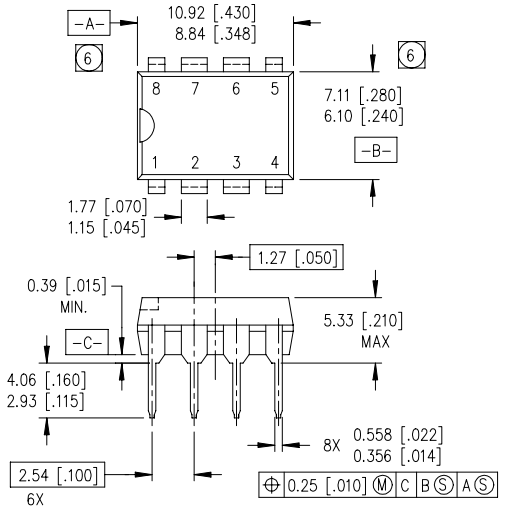


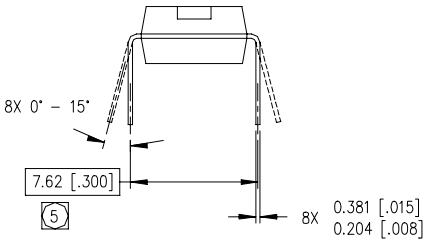
Figure 27. IRS2117/IRS2118 T_J vs. Frequency (IRFPE50)
R_{GATE} = 10 Ω, V_{CC} = 15 V

Case outlines



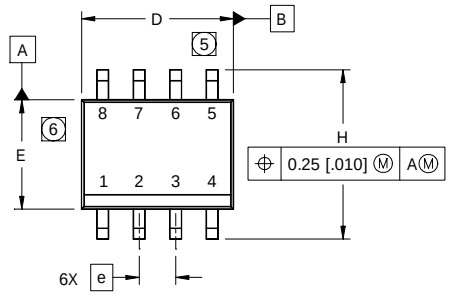
NOTES:

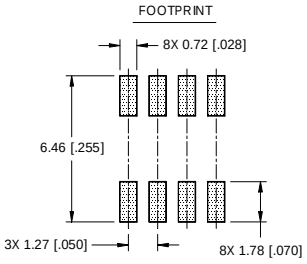
1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-001AB.
5. MEASURED WITH THE LEADS CONSTRAINED TO BE PERPENDICULAR TO DATUM PLANE C.
6. DIMENSION DOES NOT INCLUDE MOLD PROTUSIONS. MOLD PROTUSIONS SHALL NOT EXCEED 0.25 [.010].



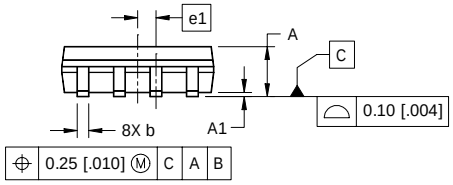
8-Lead PDIP

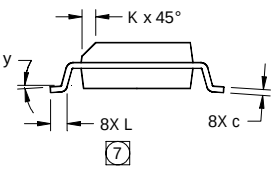
01-6014
01-3003 01 (MS-001AB)





DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e 1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°





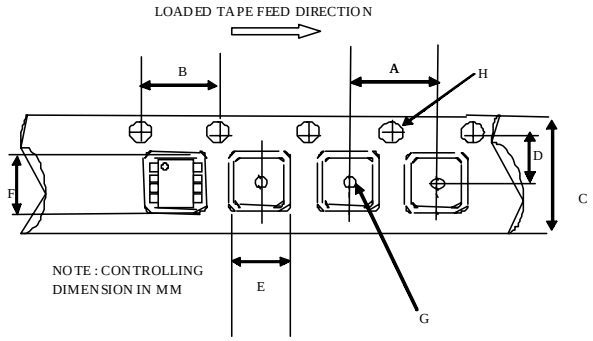
NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

01-6027

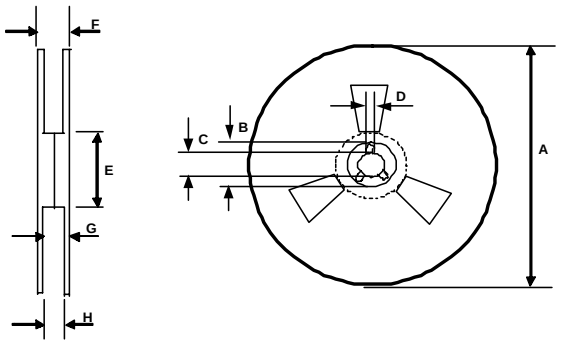
8-Lead SOIC

Tape & Reel
8-Lead SOIC



CARRIER TAPE DIMENSION FOR 8SOICN

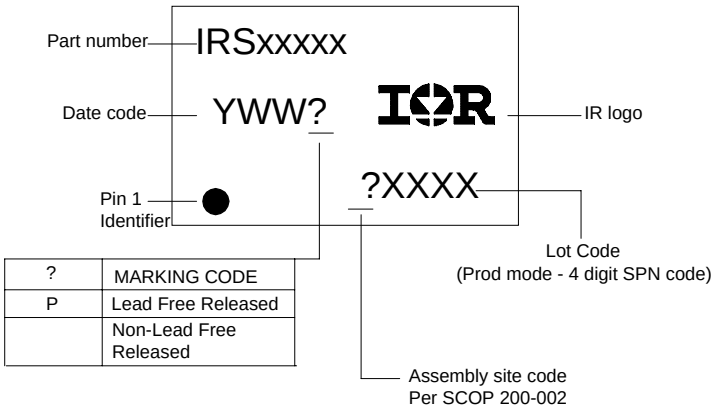
	Metric		Imperial	
Code	Min	Max	Min	Max
A	7.90	8.10	0.311	0.318
B	3.90	4.10	0.153	0.161
C	11.70	12.30	0.46	0.484
D	5.45	5.55	0.214	0.218
E	6.30	6.50	0.248	0.255
F	5.10	5.30	0.200	0.208
G	1.50	n/a	0.059	n/a
H	1.50	1.60	0.059	0.062



REEL DIMENSIONS FOR 8SOICN

	Metric		Imperial	
Code	Min	Max	Min	Max
A	329.60	330.25	12.976	13.001
B	20.95	21.45	0.824	0.844
C	12.80	13.20	0.503	0.519
D	1.95	2.45	0.767	0.096
E	98.00	102.00	3.858	4.015
F	n/a	18.40	n/a	0.724
G	14.50	17.10	0.570	0.673
H	12.40	14.40	0.488	0.566

LEADFREE PART MARKING INFORMATION



?	MARKING CODE
P	Lead Free Released
	Non-Lead Free Released

ORDER INFORMATION

8-Lead PDIP	IRS2117PbF
8-Lead PDIP	IRS2118PbF
8-Lead SOIC	IRS2117SPbF
8-Lead SOIC	IRS2118SPbF
8-Lead SOIC Tape & Reel	IRS2117STRPbF
8-Lead SOIC Tape & Reel	IRS2118STRPbF

International
IOR Rectifier

The SOIC-8 is MSL2 qualified.
This product has been designed and qualified for the industrial level.
Qualification standards can be found at www.irf.com

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245 Tel: (310) 252-7105

Data and specifications subject to change without notice. 11/20/2006